

MC74HC138A

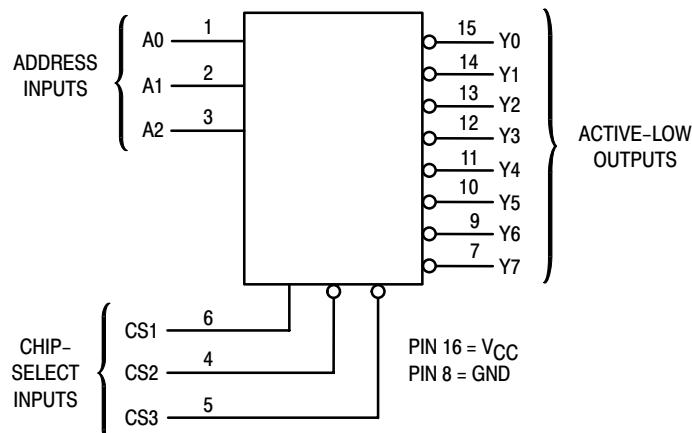
1-of-8 Decoder/ Demultiplexer High-Performance Silicon-Gate CMOS

The MC74HC138A is identical in pinout to the LS138. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSSTL outputs.

The HC138A decodes a three-bit Address to one-of-eight active-low outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

- Output Drive Capability: 10 LSSTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 100 FETs or 29 Equivalent Gates

LOGIC DIAGRAM



FUNCTION TABLE

Inputs			Outputs										
CS1	CS2	CS3	A2	A1	A0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	H	H	H	L	H	H	H	H	H	H
H	L	L	L	H	H	H	H	L	H	H	H	H	H
H	L	L	H	H	H	H	H	H	L	H	H	H	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

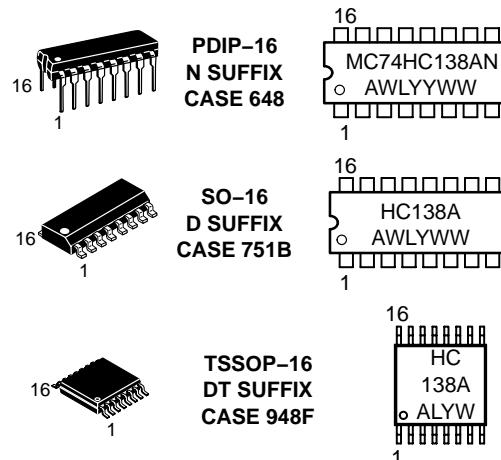
H = high level (steady state); L = low level (steady state); X = don't care



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MARKING DIAGRAMS



A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week

PIN ASSIGNMENT

A0	1 •	16	V _{CC}
A1	2	15	Y ₀
A2	3	14	Y ₁
CS2	4	13	Y ₂
CS3	5	12	Y ₃
CS1	6	11	Y ₄
Y7	7	10	Y ₅
GND	8	9	Y ₆

ORDERING INFORMATION

Device	Package	Shipping
MC74HC138AN	PDIP-16	2000 / Box
MC74HC138AD	SOIC-16	48 / Rail
MC74HC138ADR2	SOIC-16	2500 / Reel
MC74HC138ADT	TSSOP-16	96 / Rail
MC74HC138ADTR2	TSSOP-16	2500 / Reel

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	– 0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	– 0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T_{stg}	Storage Temperature	– 65 to + 150	C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: – 10 mW/ C from 65 to 125 C

SOIC Package: – 7 mW/ C from 65 to 125 C

TSSOP Package: – 6.1 .W/ C from 65 to 125 C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V	
T_A	Operating Temperature, All Package Types	– 55	+ 125	C	
t_r, t_f	Input Rise and Fall Time (Figure 2)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				–55 C to 25 C	≤ 85 C	≤ 125 C	
V_{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ or $V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ or $V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $ I_{out} \leq 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} = V_{IH}$ or V_{IL} $ I_{out} \leq 2.4 \text{ mA}$ $ I_{out} \leq 4.0 \text{ mA}$ $ I_{out} \leq 5.2 \text{ mA}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				-55 °C to 25 °C	≤ 85 °C	≤ 125 °C	
V _{OOL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 2.4 mA I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	3.0	0.26	0.33	0.40	
			4.5	0.26	0.33	0.40	
I _{IN}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I _{QC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4	40	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			-55 °C to 25 °C	≤ 85 °C	≤ 125 °C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4)	2.0	135	170	205	ns
		3.0	90	125	165	
		4.5	27	34	41	
		6.0	23	29	35	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CS1 to Output Y (Figures 2 and 4)	2.0	110	140	165	ns
		3.0	85	100	125	
		4.5	22	28	33	
		6.0	19	24	28	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CS2 or CS3 to Output Y (Figures 3 and 4)	2.0	120	150	180	ns
		3.0	90	120	150	
		4.5	24	30	36	
		6.0	20	26	31	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0	75	95	110	ns
		3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	—	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

CPD	Power Dissipation Capacitance (Per Package)*	Typical @ 25°C, V _{CC} = 5.0 V		pF
		55		

* Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{QC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

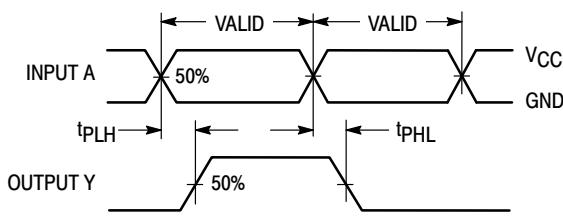


Figure 1.

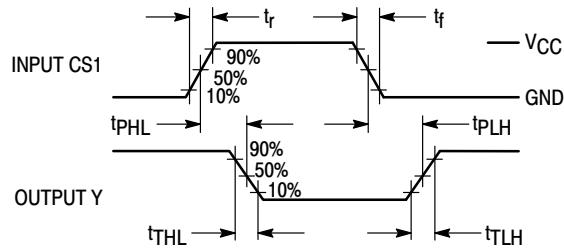


Figure 2.

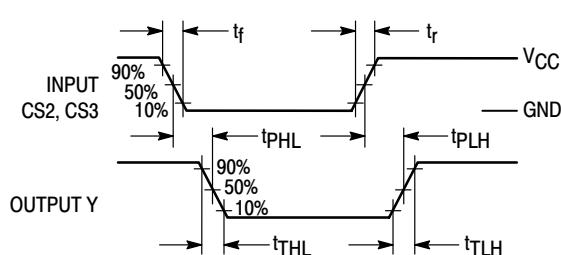
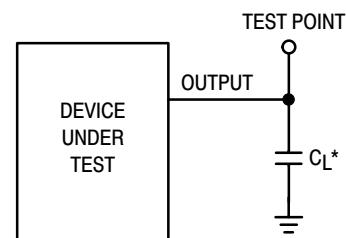


Figure 3.



*Includes all probe and jig capacitance

Figure 4. Test Circuit

PIN DESCRIPTIONS

ADDRESS INPUTS

A0, A1, A2 (Pins 1, 2, 3)

Address inputs. These inputs, when the chip is selected, determine which of the eight outputs is active-low.

CONTROL INPUTS

CS1, CS2, CS3 (Pins 6, 4, 5)

Chip select inputs. For CS1 at a high level and CS2, CS3 at a low level, the chip is selected and the outputs follow the

Address inputs. For any other combination of CS1, CS2, and CS3, the outputs are at a logic high.

OUTPUTS

Y0 – Y7 (Pins 15, 14, 13, 12, 11, 10, 9, 7)

Active-low Decoded outputs. These outputs assume a low level when addressed and the chip is selected. These outputs remain high when not addressed or the chip is not selected.

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EXPANDED LOGIC DIAGRAM

